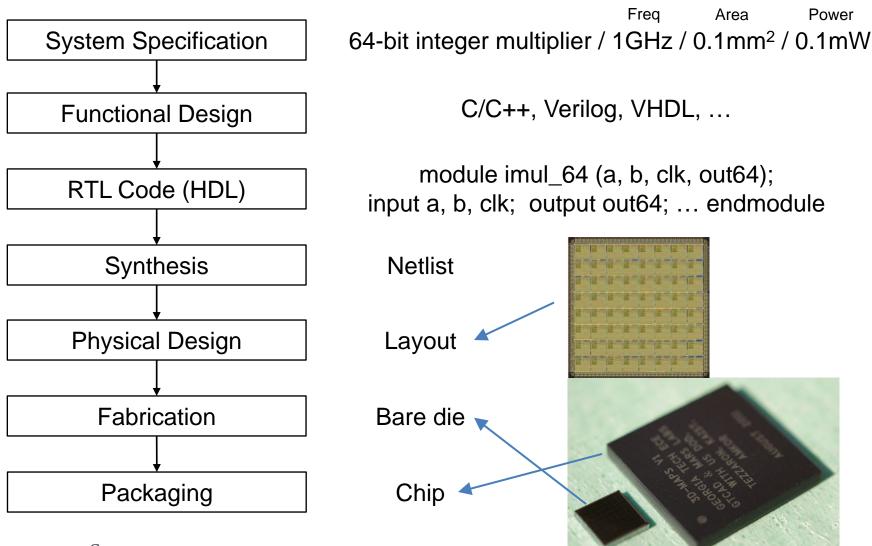
EE 434 ASIC and Digital Systems

Prof. Dae Hyun Kim
School of Electrical Engineering and Computer Science
Washington State University

Preliminaries



VLSI Design



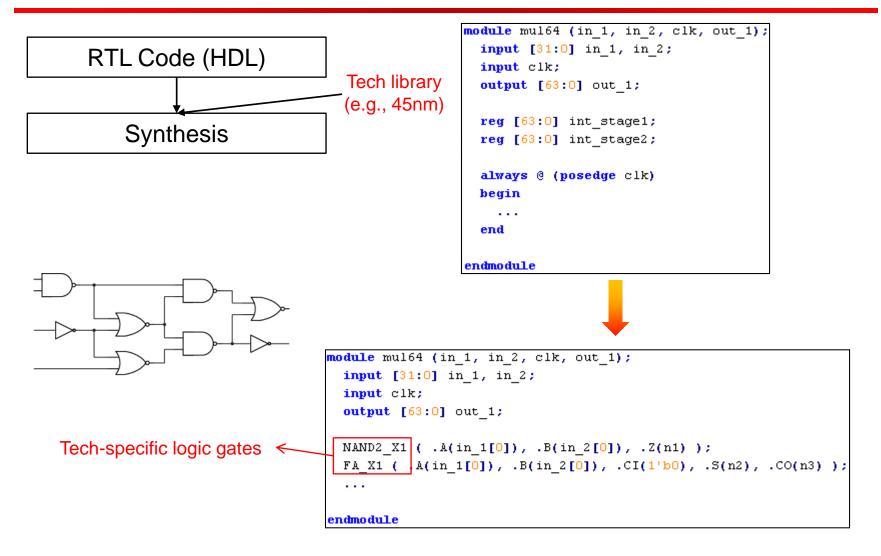
RTL Code (HDL)

```
module mul64 (in_1, in_2, clk, out_1);
  input [31:0] in_1, in_2;
  input clk;
  output [63:0] out_1;

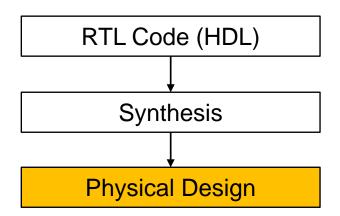
  reg [63:0] int_stage1;
  reg [63:0] int_stage2;

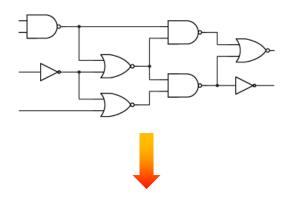
  always @ (posedge clk)
  begin
   ...
  end
endmodule
```

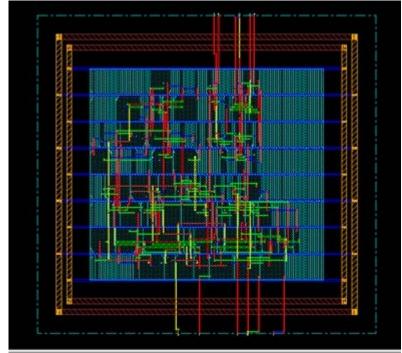




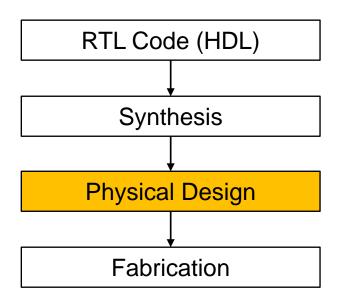




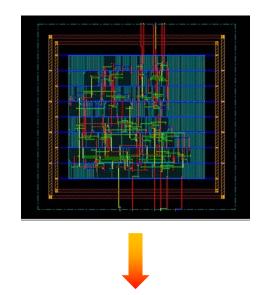


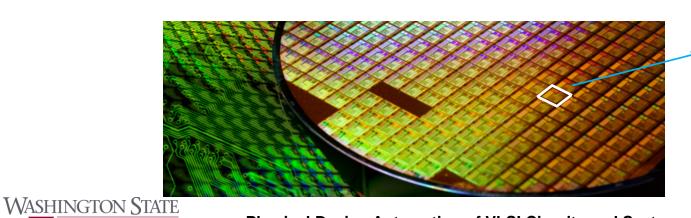


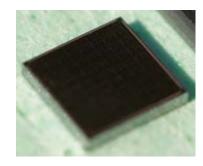


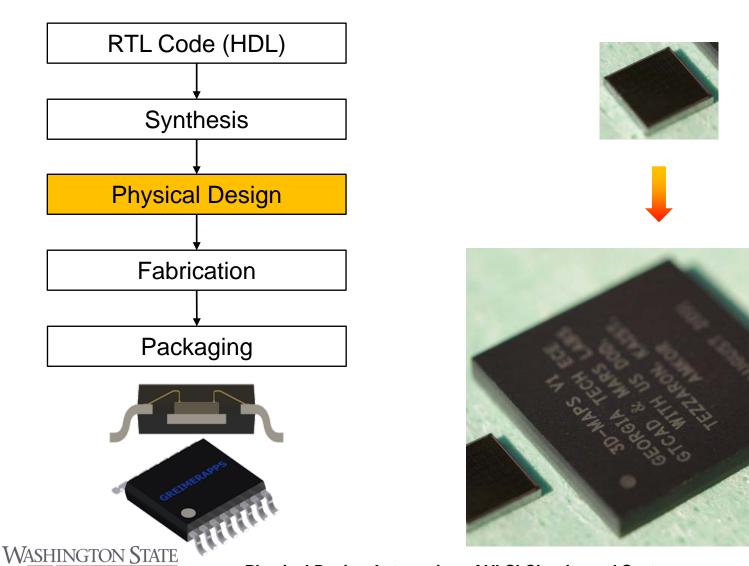


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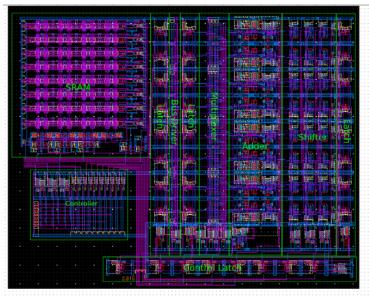


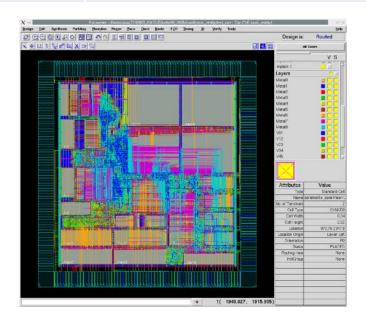


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VLSI Design

	Full custom	ASIC
Design	Manual	Automatic
TRs	Manually drawn	Standard-cell based
Placement & Routing	Custom	Automatic
Development time	Several months	A few days ~ weeks







- Provides
 - good performance
 - low power
 - small area
 - **—** ...

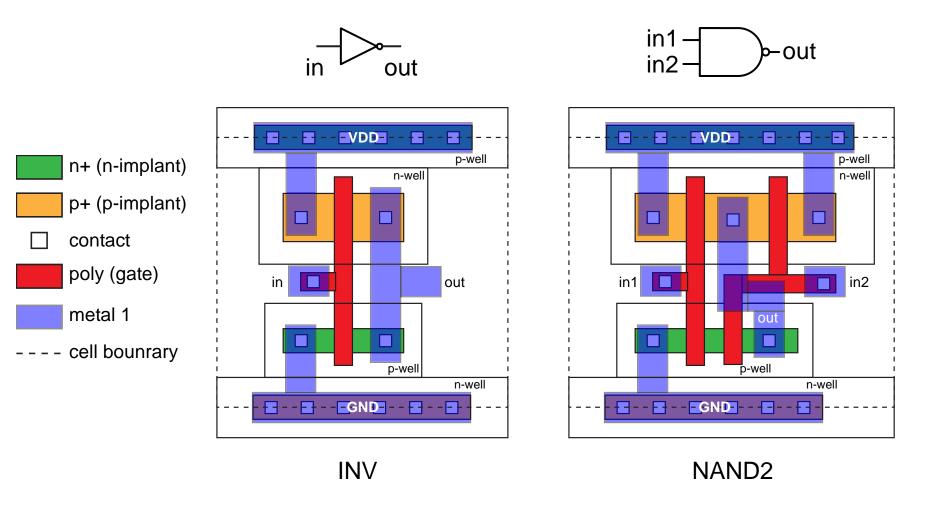
- Other design styles
 - FPGA
 - PLA
 - **—** ...



- Standard cells
 - A set of logic gates
 - Have the same height.
 - Width varies.
 - Pre-characterized for timing and power analysis.

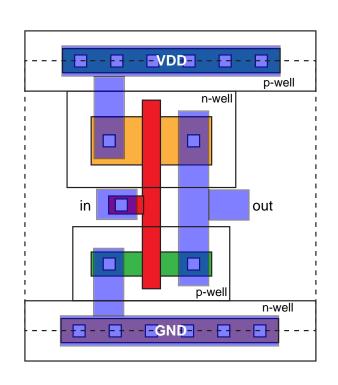


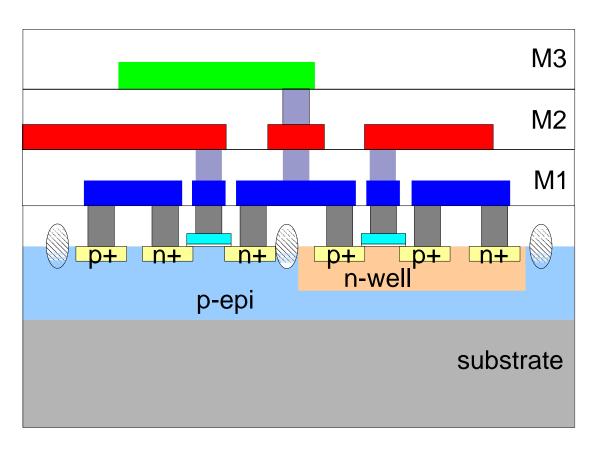
Standard Cells (Layout)





Standard Cells (Layout)



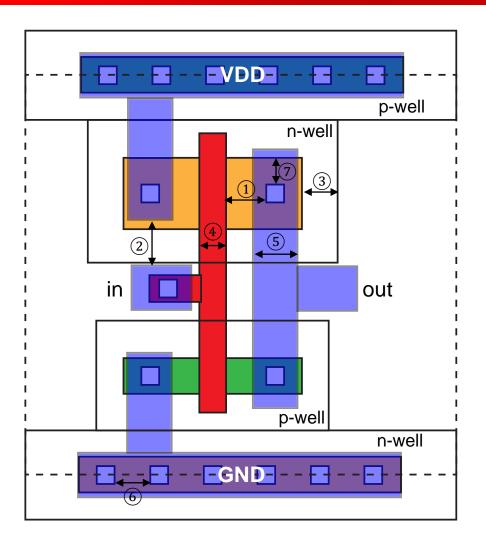


Top-down view

Side view



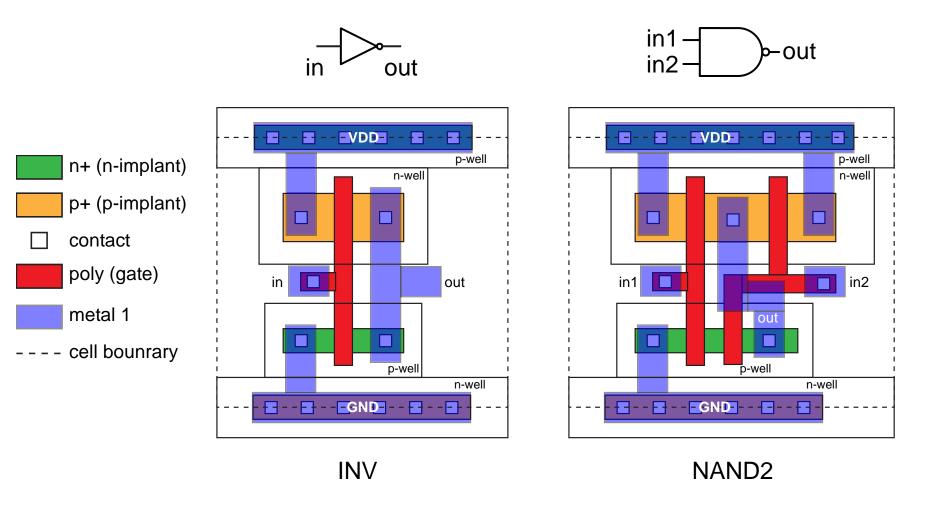
Design Rules



- 1: Min. distance (poly, contact)
- (2): Min. distance (metal 1)
- (3): Min. distance (p-active, n-well boundary)
- (4): Min. width (poly)
- (5): Min. width (metal 1)
- 6: Min. distance (contact)
- (7): Min. distance (contact, n-well bounrary)

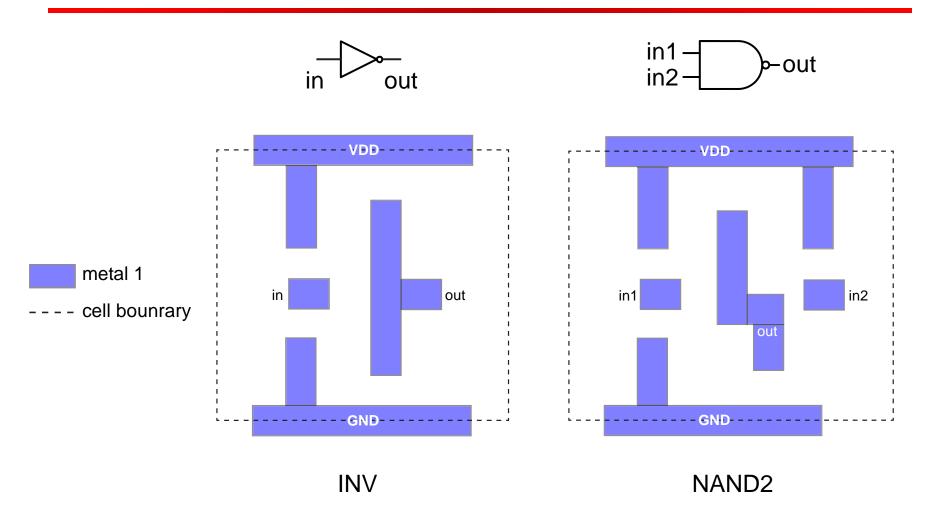


Standard Cells (Layout)

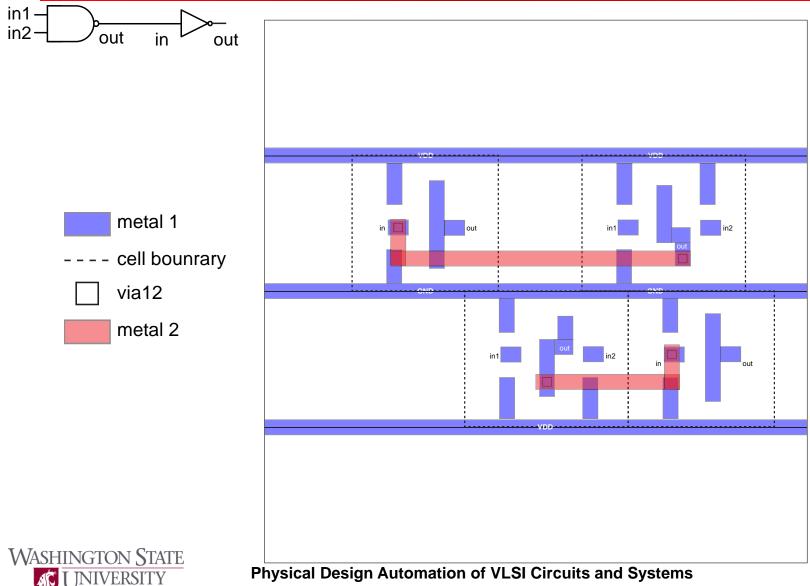




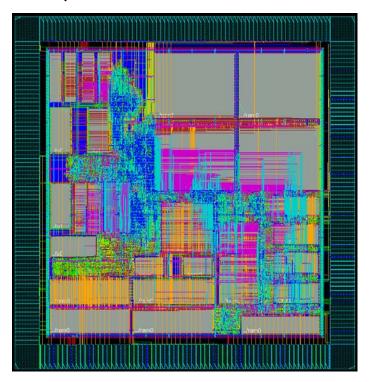
Standard Cells (Abstract)







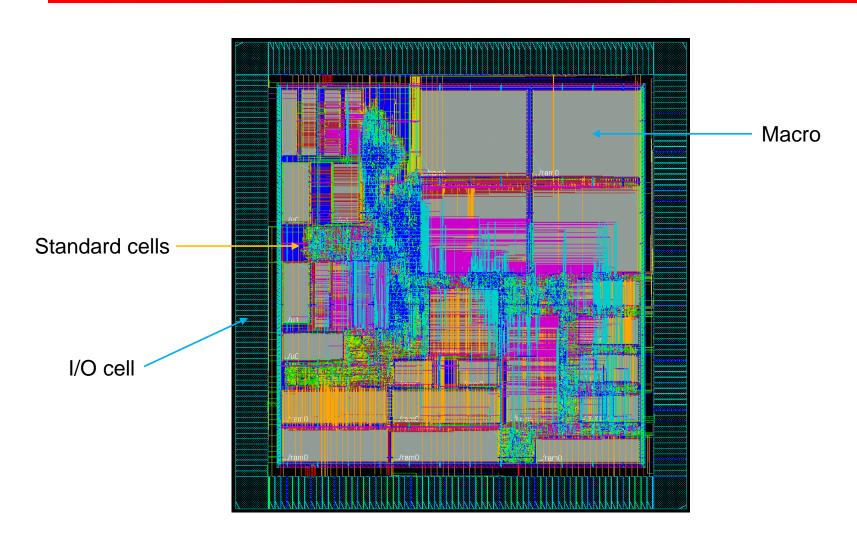
- Deal with
 - Standard cells (pre-drawn and pre-characterized)
 - Routing layers (M1, via12, M2, via23, ...)





- Intellectual Property (IP) blocks
 - Pre-created blocks
 - Memory
 - Arithmetic
 - Cryptographic
 - DSP
 - Controller
 - ...







Delay Calculation & Timing Analysis

Pre-characterized cells

```
Index_2

Input transition (ns)
Output capacitance (fF)

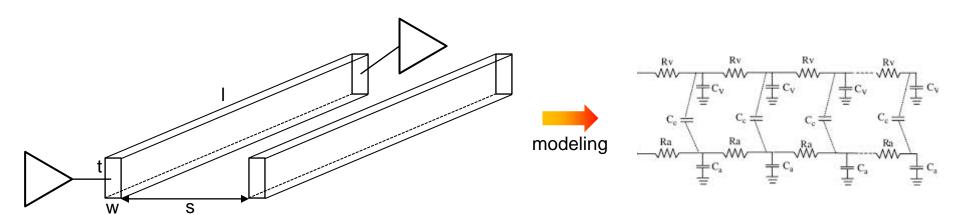
| Cell_fall(Timing_7_7) {
| index_1 ("0.00117378,0.00472397,0.0171859,0.0409838 0.0780596,0.130081,0.198535");
| output capacitance (fF) | index_2 ("0.365616,1.854900,3.709790,7.419590,14.839200,29.678300,59.356700");
| values ("0.00683090,0.0100142,0.0139116,0.0216539,0.0370876,0.0679222,0.129575", \
| "0.00801780,0.0112344,0.0151696,0.0229509,0.0384185,0.0692724,0.130935", \
| "0.0110663,0.0155786,0.0201499,0.0279195,0.0433427,0.0741885,0.135850", \
| "0.012753,0.0190883,0.0256634,0.0364481,0.0533390,0.0839029,0.145413", \
| "0.0128360,0.0209729,0.0313125,0.0483362,0.0756855,0.118141,0.182879", \
| "0.00772654,0.0192683,0.0312780,0.0512843,0.0834863,0.133996,0.210841");

| Delay (29ps)
```



Delay Calculation

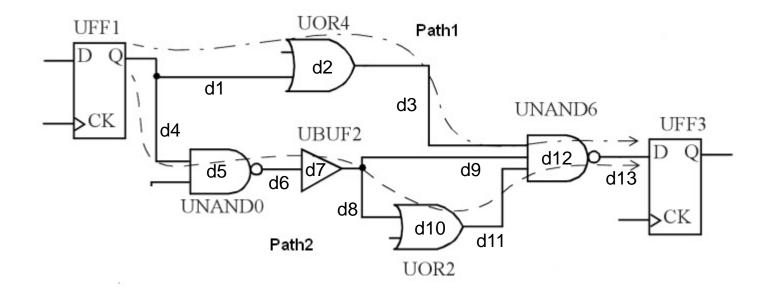
Interconnect delay



$$R = \rho \frac{l}{t \cdot w}$$
 $C = \epsilon \frac{t \cdot l}{s}$ $Delay \propto RC \propto l^2$



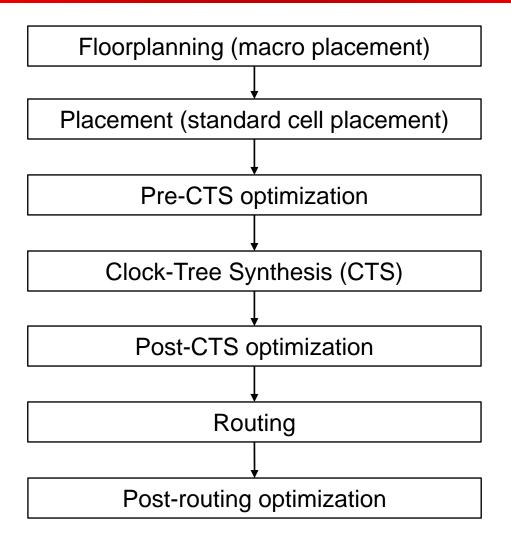
Timing Analysis



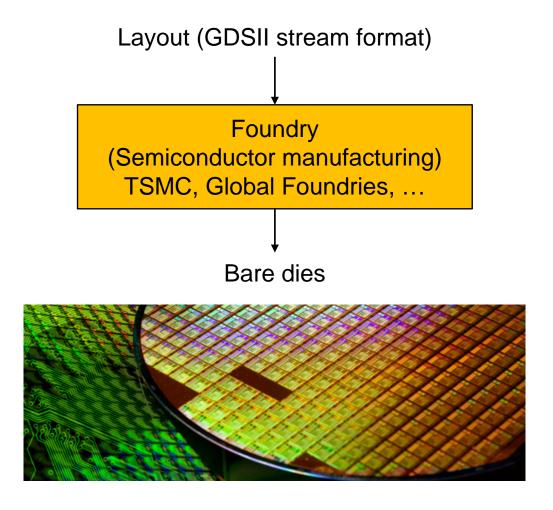


- What should we do?
 - Find the locations of the macros.
 - Find the locations of the standard cells.
 - Route the macros and the standard cells.
 - Power/ground
 - Signal
 - Clock
 - Bus
 - Extract parasitic RC.
 - Analyze the final layout.
 - Timing (clock frequency)
 - Power consumption (dynamic / leakage)
 - Area
 - Power integrity
 - Signal integrity
 - Thermal



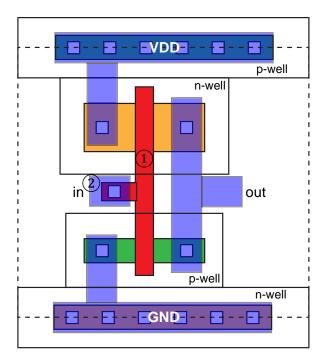






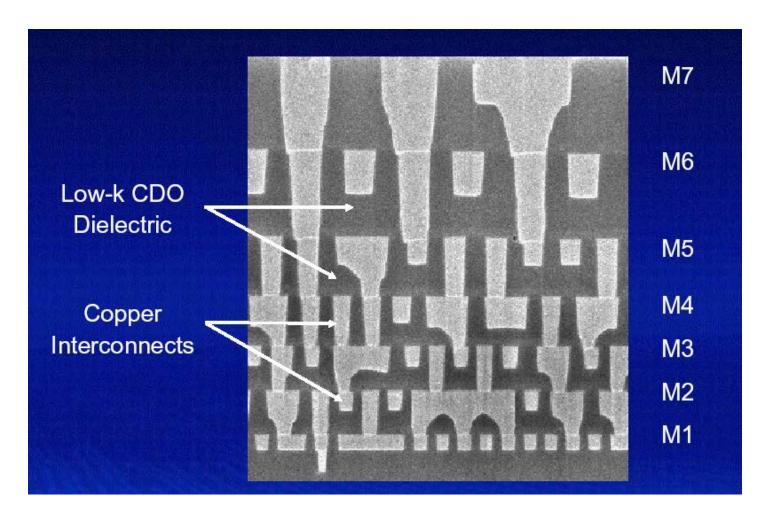


- Input
 - Layout (GDSII stream format)
 - A set of geometric objects

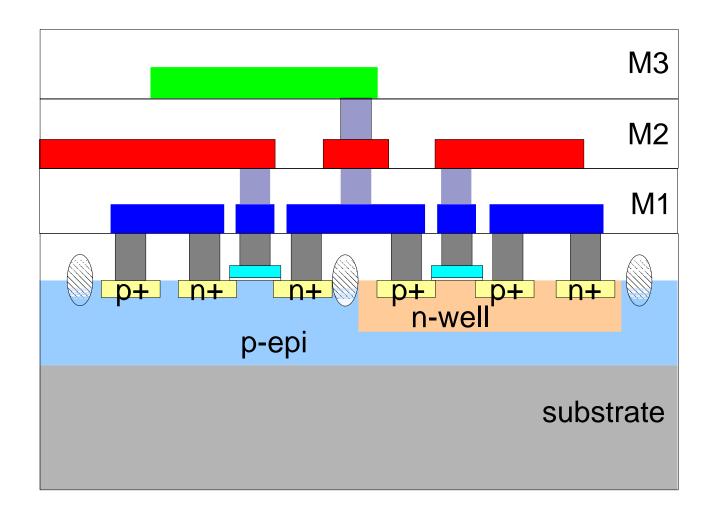


- ①: Layer id 3, polygon { 50, 40, 70, 40, 70, 220, 50, 220, 50, 140, 20, 140, 20, 110, 50, 110, 50, 40 }
- 2): Layer id 7, rectangle { 10, 105, 40, 150 }

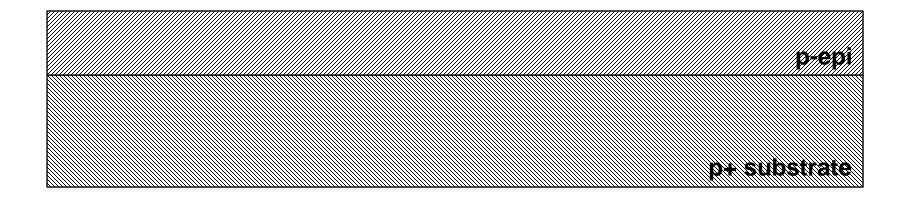




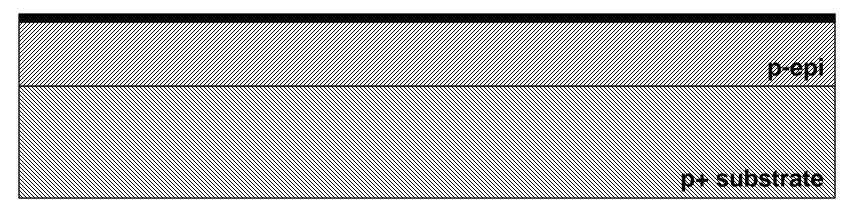








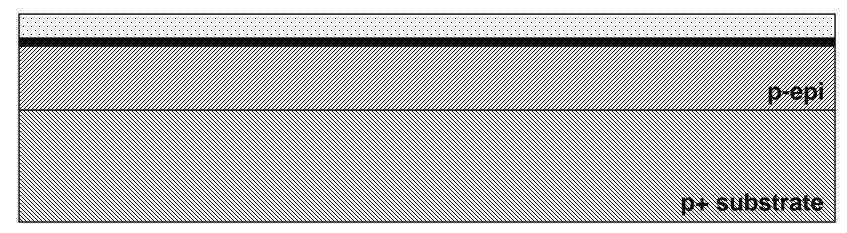




SiO₂

Gate-oxide deposition

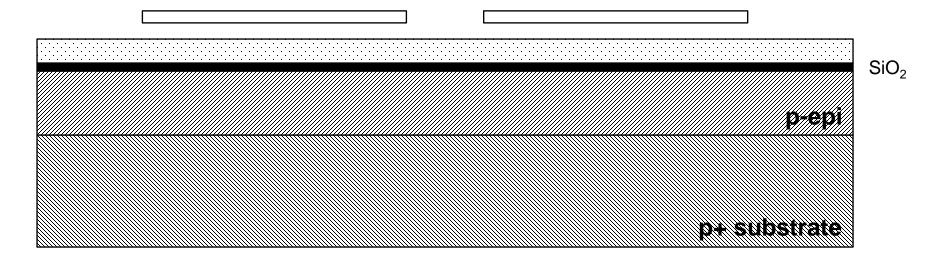




SiO₂

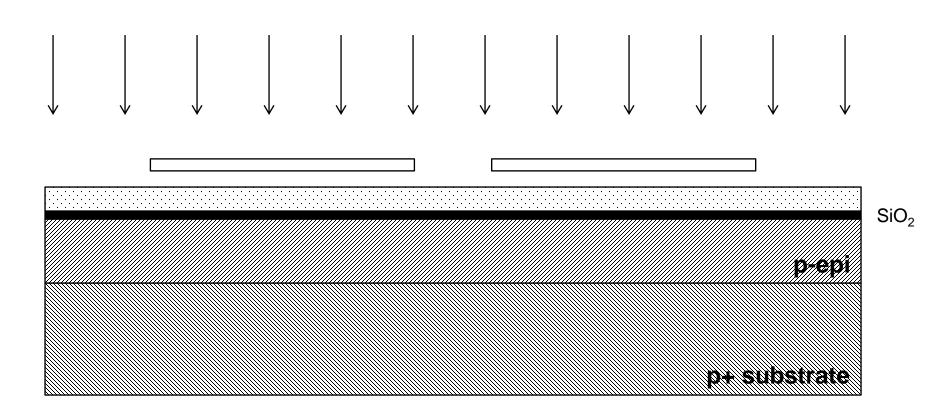
Photoresist





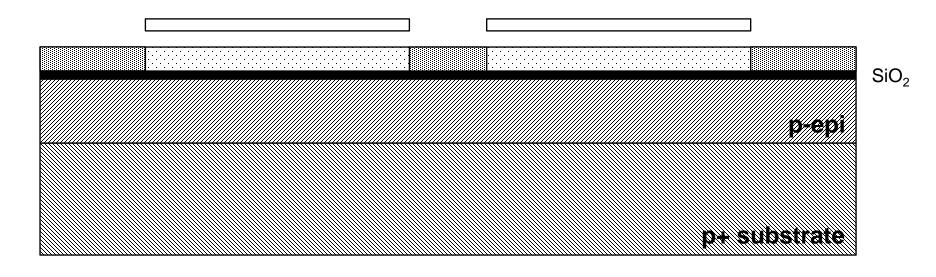
Mask





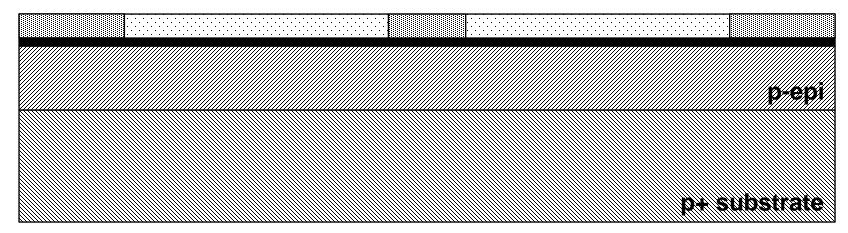
Expose (photolithography)





After photolithography

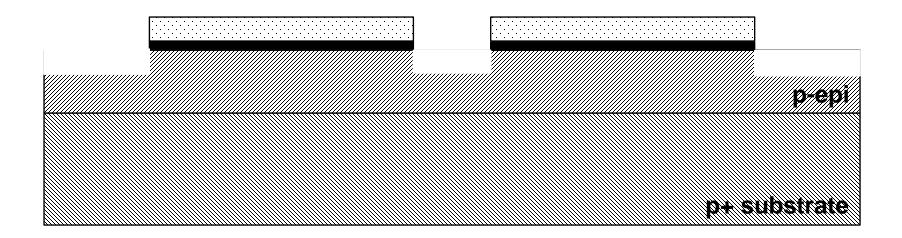




 ${\rm SiO_2}$

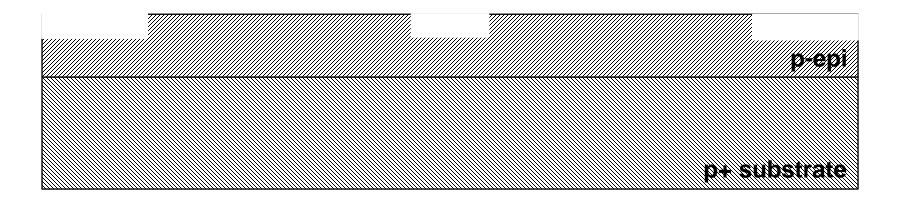
Remove mask





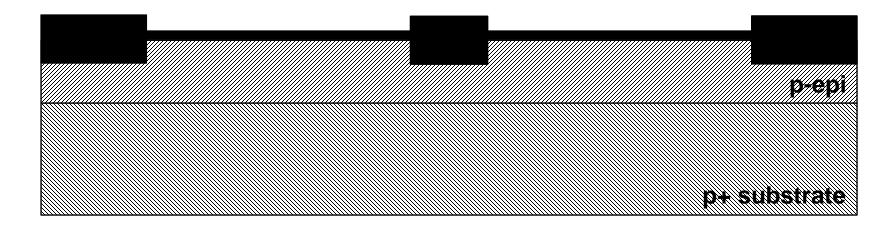
Etching





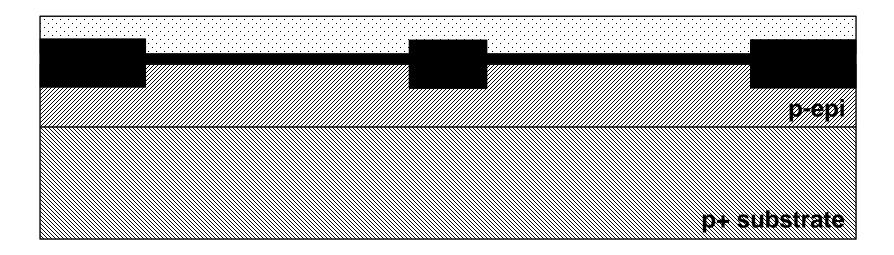
Etching





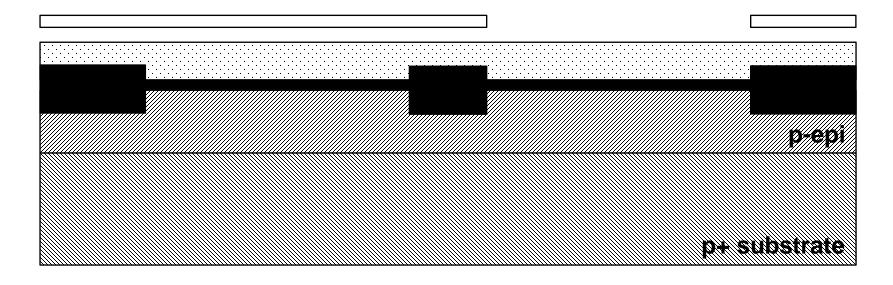
Oxide deposition





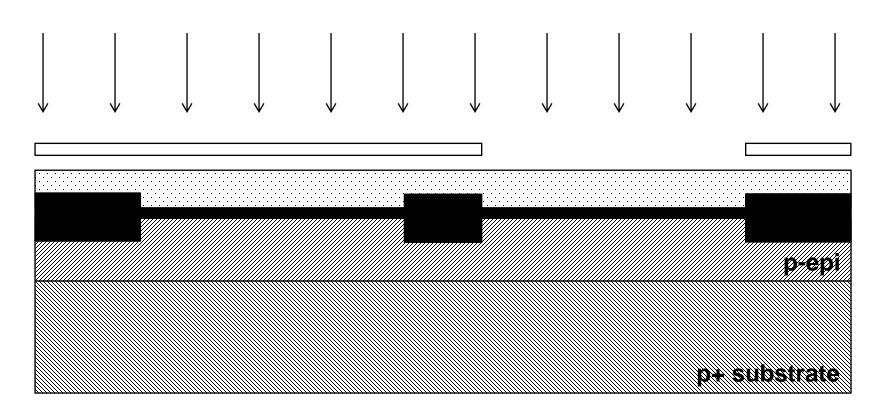
Photoresist





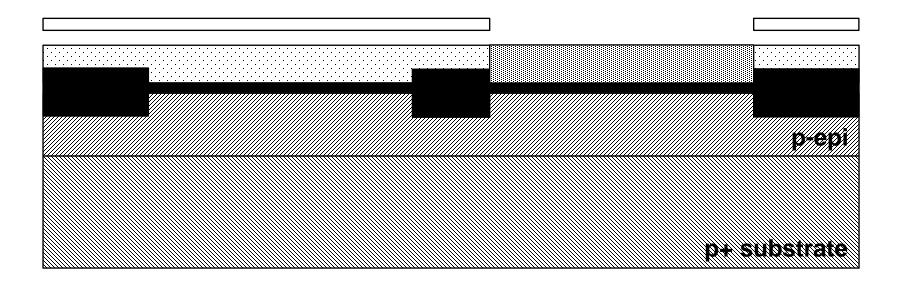






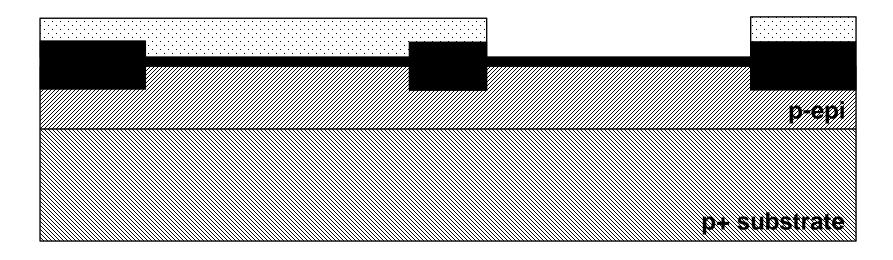
Photolithography





After photolithography

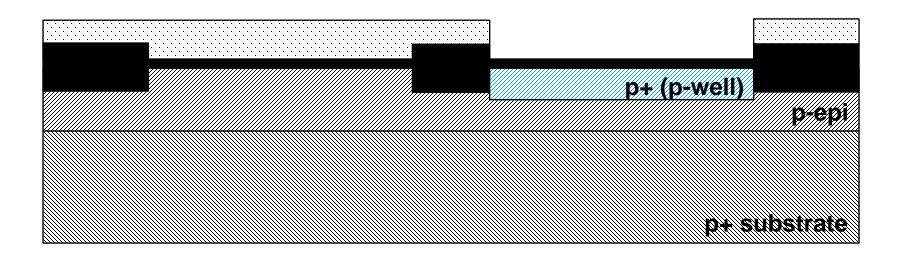




Etch

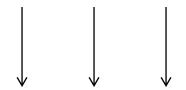


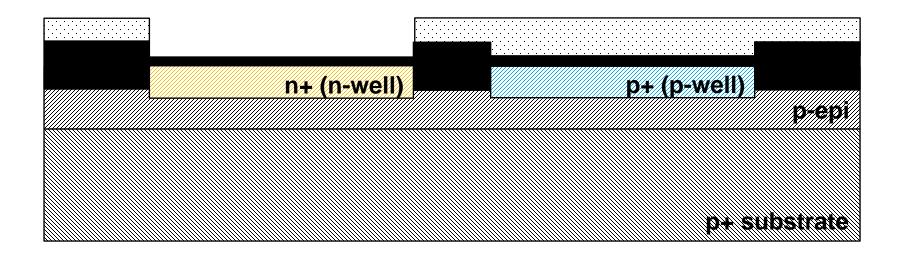




Doping

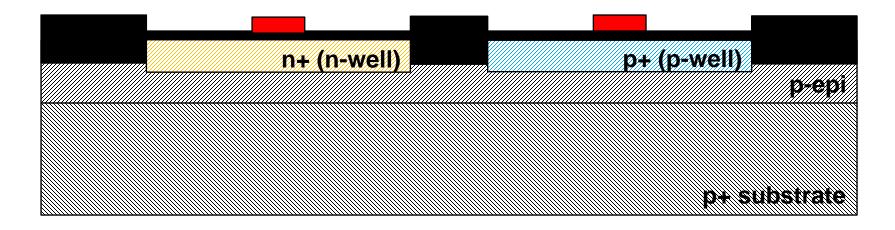






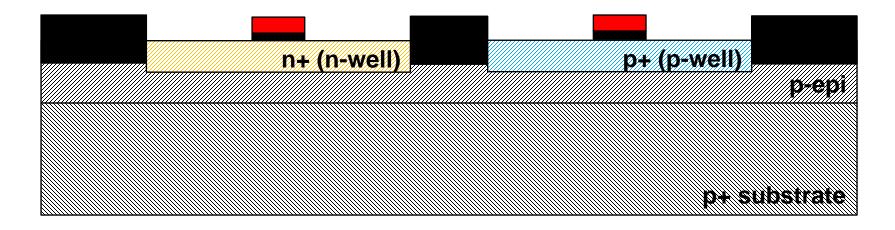
Doping





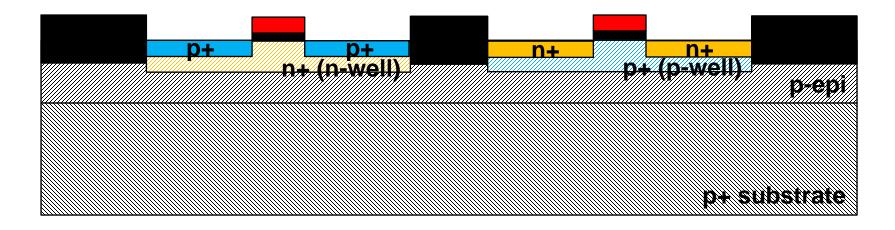
Poly





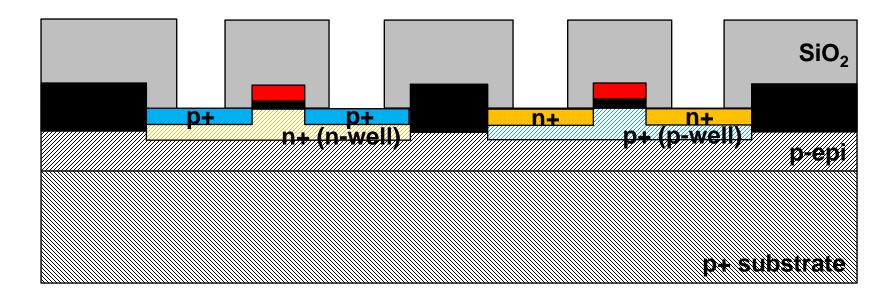
Etch





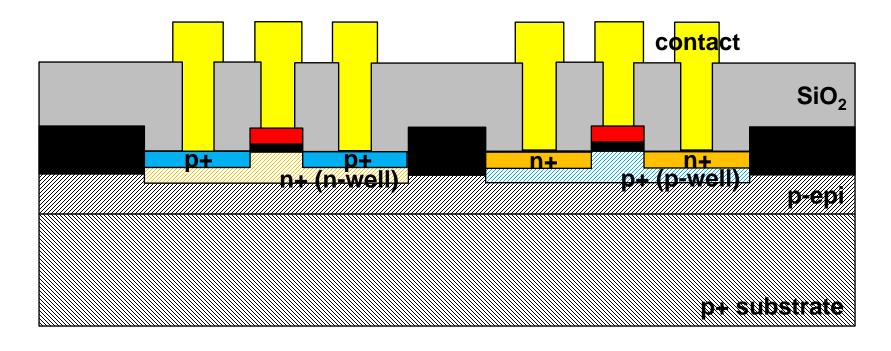
Doping





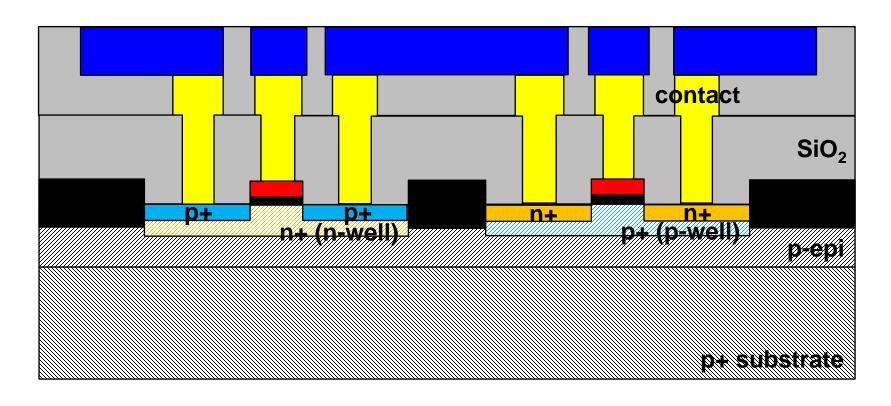
Oxide deposition





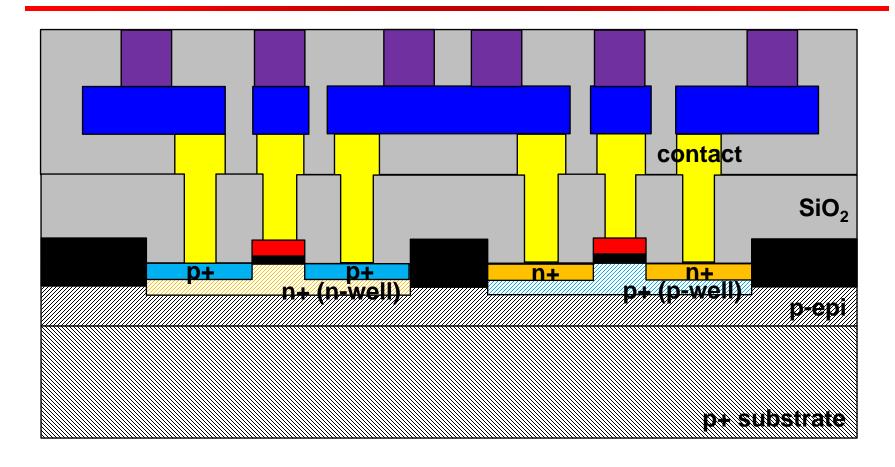
Contact





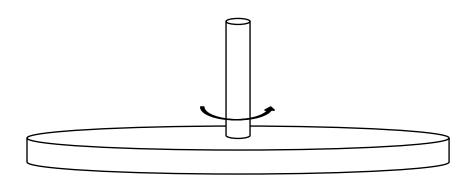
Metal 1

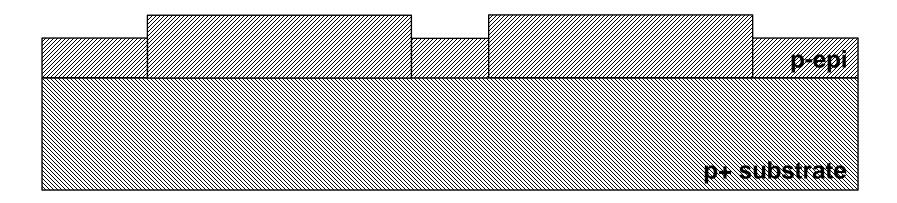




Via12







Chemical-mechanical-polishing (CMP)



